



Bipolar PNP Bare Die – BTP6085

Part Description

The BTP6085 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6085

Key Parameters:

- VCBO = -40V
- VCEO = -25V
- VEBO = -6V
- hFE = 85-300 @ VCE = -1V, IC = -0.1A
- VCE(Sat) = -0.5V @ IC = -0.8A, IB = -80mA
- fT = 100 MHz @ VCE = -10V, IE = 0A
- COBO = 10pF @ VCB = -10V

Features

Low VCE(sat). Designed to provide performance equivalent to ON Semi SS8550

Die Size (Unawn)

450µm X 450µm, 18 Mils X 18 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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